Silicon NPN Power Transistors

2SC4544

DESCRIPTION

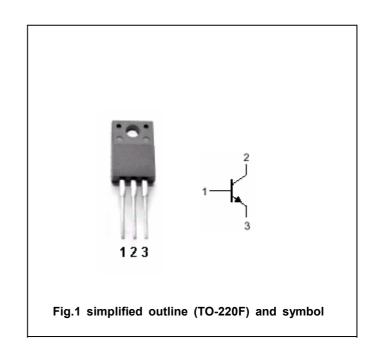
- ·With TO-220F package
- ·High Voltage

APPLICATIONS

- ·Color TV horizontal driver applications
- ·Color TV chroma output applications

PINNING

PIN	DESCRIPTION			
1	Base			
2	Collector			
3	Emitter			



Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	300	V	
V _{CEO}	Collector-emitter voltage	Open base	300	V	
V _{EBO}	Emitter-base voltage	Open collector	7	V	
Ic	Collector current		100	mA	
I _B	Base current		50	mA	
P _C	Collector power dissipation	T _a =25□	2	W	
		T _C =25□	8		
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-55~150		

Silicon NPN Power Transistors

2SC4544

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100μA; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA ;I _B =1m A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I _C =10mA ;I _B =1m A			1.0	V
h _{FE-1}	DC current gain	I _C =4mA; V _{CE} =10V	20			
h _{FE-2}	DC current gain	I _C =20mA ; V _{CE} =10V	30		200	
I _{CBO}	Collector cut-off current	V _{CB} =240V; I _E =0			1.0	μΑ
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	μA
Сов	Output capacitance	I _E =0; V _{CB} =20V;f=1MHz		3		pF
f _T	Transition frequency	I _C =20mA ; V _{CE} =10V	50	70		MHz

Silicon NPN Power Transistors

2SC4544

PACKAGE OUTLINE

